

January 2007

# FAN7384 Half-Bridge Gate-Drive IC

#### **Features**

- Floating Channel for Bootstrap Operation to +600V
- Typically 250mA/500mA Sourcing/Sinking Current Driving Capability for Both Channels
- Extended Allowable Negative V<sub>S</sub> Swing to -9.8V for Signal Propagation at V<sub>DD</sub>=V<sub>BS</sub>=15V
- Matched Propagation Delay Below 50ns
- Output In-Phase with Input Signal
- 3.3V and 5V Input Logic Compatible
- Built-in Shoot-Through Prevention Logic
- Built-in Common Mode dv/dt Noise Canceling Circuit
- Built-in UVLO Functions for Both Channels
- Built-in Cycle-by-Cycle Shutdown Function
- Built-in Soft-Off Function
- Built-in Bi-Directional Fault Function
- Built-in Short-Circuit Protection Function

### **Applications**

- Motor Inverter Driver
- Normal Half-Bridge and Full-Bridge Driver
- Switching Mode Power Supply

### **Description**

The FAN7384 is a monolithic half-bridge gate-drive IC designed for high voltage, high speed driving MOSFETs and IGBTs operating up to +600V.

Fairchild's high-voltage process and common-mode noise canceling technique provide stable operation of high-side drivers under high-dv/dt noise circumstances.

An advanced level-shift circuit allows high-side gate driver operation up to  $V_S$  = -9.8V (typical) for  $V_{BS}$  =15V.

The UVLO circuits prevent malfunction when  $V_{DD}$  and  $V_{BS}$  are lower than the specified threshold voltage.

Output drivers typically source/sink 250mA/500mA, respectively, which is suitable for half-bridge and full-bridge applications in motor drive systems.

14-SOP



## Ordering Information

Part Number	Package	Pb-Free	Operating Temperature Range	Packing Method
FAN7384M <sup>(1)</sup>	14-SOP	Yes	-40°C ~ 125°C	Tube
FAN7384MX <sup>(1)</sup>	AN7384MX <sup>(1)</sup>		-40 0 * 125 0	Tape & Reel

#### Note:

1. These devices passed wave soldering test by JESD22A-111.

## **Typical Application Diagrams**

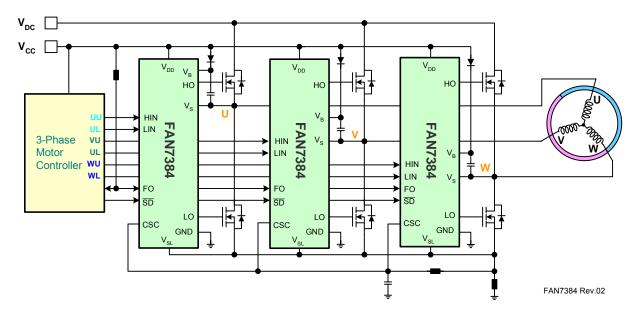


Figure 1. 3-Phase Motor Drive Application

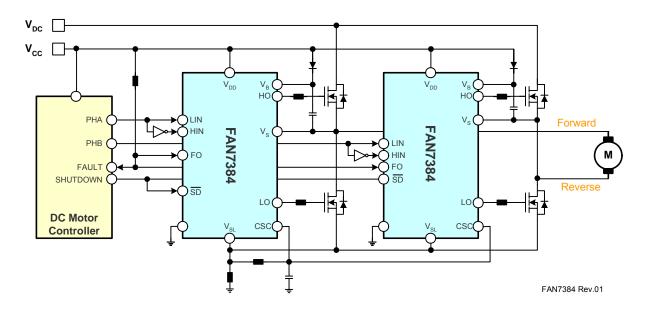


Figure 2. DC Motor Drive Application

## **Internal Block Diagram**

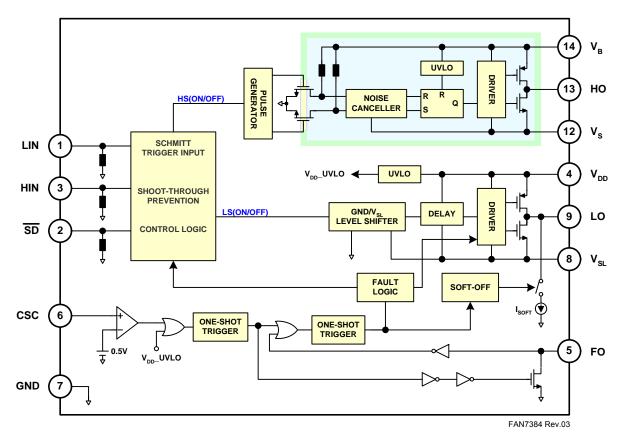


Figure 3. Functional Block Diagram

## **Pin Configuration**

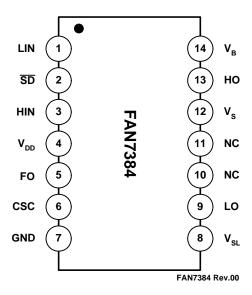


Figure 4. Pin Configuration (Top View)

## **Pin Definitions**

Pin #	Name	Description	
1	LIN	Logic Input for low-side gate driver	
2	SD	Shutdown control input with active low	
3	HIN	Logic Input for high-side gate driver	
4	$V_{DD}$	Low-side power supply voltage	
5	FO	Bi-direction fault pin with open drain	
6	CSC	Short-circuit current detection input	
7	GND	Ground	
8	V <sub>SL</sub>	Low-side supply offset voltage	
9	LO	Low-side gate driver output	
10	NC	No connection	
11	NC	No connection	
12	V <sub>S</sub>	High-side floating supply offset voltage	
13	НО	High-side gate driver output	
14	V <sub>B</sub>	High-side floating supply voltage	

### **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A=25^{\circ}C$ , unless otherwise specified.

Symbol	Parameter	Min.	Max.	Unit
V <sub>S</sub>	High-side offset voltage V <sub>S</sub>	V <sub>B</sub> -25	V <sub>B</sub> +0.3	V
V <sub>B</sub>	High-side floating supply voltage V <sub>B</sub>	-0.3	625	V
V <sub>HO</sub>	High-side floating output voltage	V <sub>S</sub> -0.3	V <sub>B</sub> +0.3	V
V <sub>DD</sub>	Low-side and logic-fixed supply voltage	-0.3	25	V
V <sub>IN</sub>	Logic input voltage (HIN, LIN, SD)	-0.3	V <sub>DD</sub> +0.3	V
V <sub>CSC</sub>	Current sense input voltage	-0.3	V <sub>DD</sub> +0.3	V
V <sub>FO</sub>	Fault output voltage	-0.3	V <sub>DD</sub> +0.3	V
dV <sub>S</sub> /dt	Allowable offset voltage slew rate		50	V/ns
P <sub>D</sub> <sup>(2)(3)(4)</sup>	P <sub>D</sub> <sup>(2)(3)(4)</sup> Power dissipation		1.0	W
$\theta_{JA}$	Thermal resistance, junction-to-ambient		110	°C/W
TJ	Junction temperature		150	°C
T <sub>S</sub>	Storage temperature	-55	150	°C

#### Notes:

- 2. Mounted on 76.2 x 114.3 x 1.6mm PCB (FR-4 glass epoxy material).
- 3. Refer to the following standards:
  - JESD51-2: Integral circuits thermal test method environmental conditions natural convection JESD51-3: Low effective thermal conductivity test board for leaded surface mount packages
- 4. Do not exceed P<sub>D</sub> under any circumstances.

## **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Condition	Min.	Max.	Unit
V <sub>B</sub>	High-side floating supply voltage		V <sub>S</sub> +13	V <sub>S</sub> +20	V
V <sub>S</sub>	High-side floating supply offset voltage		6-V <sub>DD</sub>	600	V
$V_{DD}$	Supply voltage		13	20	V
V <sub>HO</sub>	High-side output voltage		V <sub>S</sub>	V <sub>B</sub>	V
V <sub>LO</sub>	Low-side output voltage		GND	$V_{DD}$	V
V <sub>IN</sub>	Logic input voltage (HIN, LIN, SD)		GND	$V_{DD}$	V
V <sub>FO</sub>	Fault output voltage		-0.3	V <sub>DD</sub> +0.3	V
T <sub>A</sub>	Ambient temperature		-40	125	°C

### **Electrical Characteristics**

 $V_{BIAS}$  ( $V_{DD}$ ,  $V_{BS}$ ) = 15.0V,  $T_A$  = 25°C, unless otherwise specified. The  $V_{IN}$  and  $I_{IN}$  parameters are referenced to GND. The  $V_O$  and  $I_O$  parameters are referenced to GND and  $V_S$  is applicable to HO and LO.

Symbol	Characteristics	Condition	Min.	Тур.	Max.	Unit
LOW SIDE	POWER SUPPLY SECTION		•			•
$I_{QDD}$	Quiescent V <sub>DD</sub> supply current	V <sub>LIN</sub> =0V or 5V		600	800	μА
I <sub>PDD</sub>	Operating V <sub>DD</sub> supply current	f <sub>LIN</sub> =20kHz, rms value		950	1300	μА
V <sub>DDUV+</sub>	V <sub>DD</sub> supply under-voltage positive going threshold	V <sub>DD</sub> =Sweep	10.9	11.9	12.9	٧
V <sub>DDUV-</sub>	$V_{DD}$ supply under-voltage negative going threshold	V <sub>DD</sub> =Sweep	10.4	11.4	12.4	٧
V <sub>DDHYS</sub>	V <sub>DD</sub> supply under-voltage lockout hysteresis	V <sub>DD</sub> =Sweep		0.5		٧
BOOTSTE	RAPPED POWER SUPPLY SECTION			u.		
V <sub>BSUV+</sub>	V <sub>BS</sub> supply under-voltage positive going threshold	V <sub>BS</sub> =Sweep	10.6	11.5	12.4	٧
V <sub>BSUV</sub> -	V <sub>BS</sub> supply under-voltage negative going threshold	V <sub>BS</sub> =Sweep	10.1	11.0	11.9	٧
V <sub>BSHYS</sub>	V <sub>BS</sub> supply under-voltage lockout hysteresis	V <sub>BS</sub> =Sweep		0.5		V
I <sub>LK</sub>	Offset supply leakage current	V <sub>B</sub> =V <sub>S</sub> =600V			10	μА
$I_{QBS}$	Quiescent V <sub>BS</sub> supply current	V <sub>HIN</sub> =0V or 5V		50	90	μА
I <sub>PBS</sub>	Operating V <sub>BS</sub> supply current	f <sub>HIN</sub> =20kHz, rms value		400	600	μА
GATE DR	IVER OUTPUT SECTION					
V <sub>OH</sub>	High-level output voltage, V <sub>BIAS</sub> -V <sub>O</sub>	I <sub>O</sub> =0mA (No Load)			100	mV
V <sub>OL</sub>	Low-level output voltage, V <sub>O</sub>	I <sub>O</sub> =0mA (No Load)			100	mV
I <sub>O+</sub>	Output HIGH short-circuit pulse current	V <sub>O</sub> =0V, V <sub>IN</sub> =5V with PW<10μs	200	250		mA
I <sub>O-</sub>	Output LOW short-circuit pulsed current	V <sub>O</sub> =15V, V <sub>IN</sub> =0V with PW<10μs	420	500		mA
V <sub>S</sub>	Allowable negative V <sub>S</sub> pin voltage for IN signal propagation to H <sub>O</sub>			-9.8	-7.0	٧
V <sub>SL</sub> -GND	V <sub>SL</sub> -GND/GND-V <sub>SL</sub> voltage educability		-7.0		7.0	V
SHUTDO	WN CONTROL SECTION (SD)					
SD+	Shutdown "1" input voltage				1.2	V
SD-	Shutdown "0" input voltage		2.5			V
LOGIC IN	PUT SECTION (HIN, LIN)	•		•		•
$V_{IH}$	Logic "1" input voltage		2.5			V
$V_{IL}$	Logic "0" input voltage				1.2	V
V <sub>INHYS</sub>	Logic input hysteresis voltage			0.5		V
I <sub>IN+</sub>	Logic "1" input bias current	V <sub>IN</sub> =5V	10	15	20	μА
I <sub>IN-</sub>	Logic "0" input bias current	V <sub>IN</sub> =0V			2.0	μА

### **Electrical Characteristics** (Continued)

 $V_{BIAS}$  ( $V_{DD}$ ,  $V_{BS}$ ) = 15.0V,  $T_A$  = 25°C, unless otherwise specified. The  $V_{IN}$  and  $I_{IN}$  parameters are referenced to GND. The  $V_O$  and  $I_O$  parameters are referenced to GND and  $V_S$  is applicable to HO and LO.

Symbol	Characteristics	Condition	Min.	Тур.	Max.	Unit
SHORT-C	SHORT-CIRCUIT PROTECTION					
V <sub>CSCREF</sub>	Short-circuit detector reference voltage		0.47	0.50	0.53	V
I <sub>CSCIN</sub>	Short-circuit input current	V <sub>CSCIN</sub> =1V, R <sub>CSCIN</sub> =100KΩ	5	10	15	μΑ
I <sub>SOFT</sub>	Soft turn-off source current	V <sub>DD</sub> =15V	5	10	15	mA
-V <sub>CSC</sub>	Negative CSC pin immunity <sup>(5)</sup>	Voltage on CSC pin up to -12V, Time<2µs			-20	٧
FAULT DI	ETECTION SECTION					
V <sub>FINH</sub>	Fault input high level voltage		2.5			V
V <sub>FINL</sub>	Fault input low level voltage				1.2	V
V <sub>FINHYS</sub>	Fault input hysteresis voltage <sup>(5)</sup>			0.5		V
V <sub>FOH</sub>	Fault output high level voltage	$V_{CSC}$ =0V, $R_{PULL-UP}$ =4.7K $\Omega$	4.7			V
V <sub>FOL</sub>	Fault output low level voltage	V <sub>CSC</sub> =1V, I <sub>FO</sub> =2mA	•		8.0	V
t <sub>FO</sub>	Fault output pulse width	V <sub>CSCIN</sub> =1V	•	60	100	μs

#### Note:

5. These parameters, although guaranteed, not 100% tested in production.

## **Dynamic Electrical Characteristics**

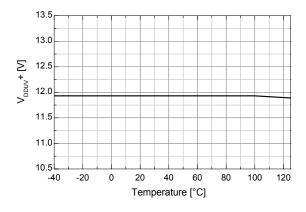
 $T_A$ =25°C,  $V_{BIAS}$  ( $V_{DD}$ ,  $V_{BS}$ ) = 15.0V,  $V_S$  = GND,  $C_{Load}$  = 1000pF unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
t <sub>on</sub>	Turn-on propagation delay	V <sub>S</sub> =0V		180	260	ns
t <sub>off</sub>	Turn-off propagation delay	V <sub>S</sub> =0V		170	240	ns
t <sub>r</sub>	Turn-on rise time			50	100	ns
t <sub>f</sub>	Turn-off fall time			30	80	ns
MT	Delay matching				50	ns
DT	Dead-time		80	120	170	ns
t <sub>UVFLT</sub>	Under-voltage filtering time <sup>(6)</sup>			16		μs
t <sub>CSCFLT</sub>	CSC pin filtering time <sup>(6)</sup>			300		ns
t <sub>CSCFO</sub>	Time from CSC triggering to FO <sup>(6)</sup>			350		ns
tcsclo	Time from CSC triggering to low-side gate $\operatorname{output}^{(6)}$	From V <sub>CSC</sub> =1V to starting gate turn-off		600		ns
t <sub>SDFO</sub>	Shutdown to FO propagation delay <sup>(6)</sup>			60		ns
t <sub>SDOFF</sub>	Shutdown to HIGH/LOW-side gate off <sup>(6)</sup>			100		ns

#### Note:

6. These parameters, although guaranteed, not 100% tested in production.

## **Typical Characteristics**



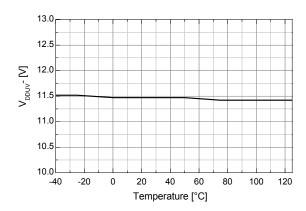
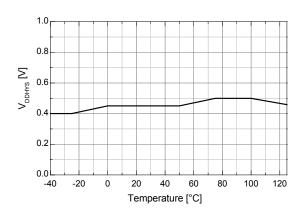


Figure 5.  $V_{DD}$  UVLO (+) vs. Temperature

Figure 6. V<sub>DD</sub> UVLO (-) vs. Temperature



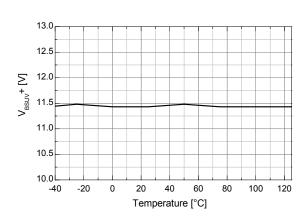
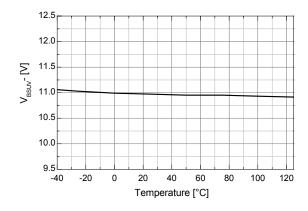


Figure 7.  $V_{DD}$  UVLO Hysteresis vs. Temperature

Figure 8. V<sub>BS</sub> UVLO (+) vs. Temperature



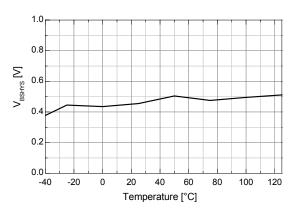
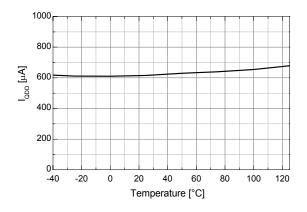


Figure 9.  $V_{BS}$  UVLO (-) vs. Temperature

Figure 10.  $V_{BS}$  UVLO Hysteresis vs. Temperature



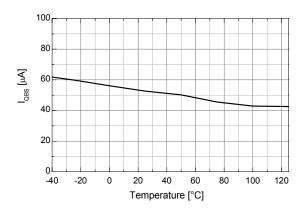
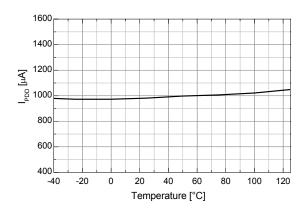


Figure 11. V<sub>DD</sub> Quiescent Current vs. Temperature

Figure 12. V<sub>BS</sub> Quiescent Current vs. Temperature



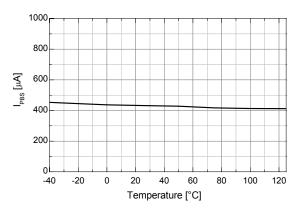
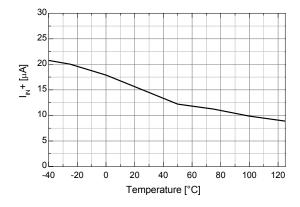


Figure 13.  $V_{DD}$  Operating Current vs. Temperature

Figure 14. V<sub>BS</sub> Operating Current vs. Temperature



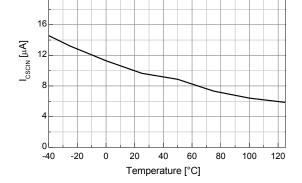
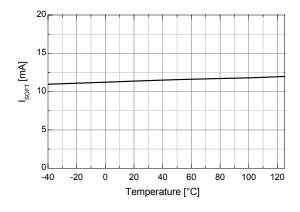


Figure 15. Logic Input Current vs. Temperature

Figure 16.  $I_{CSCIN}$  vs. Temperature



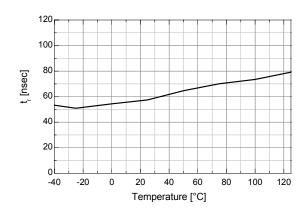
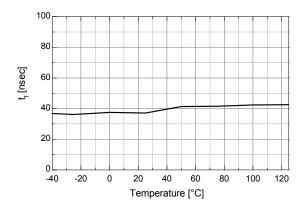


Figure 17.  $I_{SOFT}$  vs. Temperature

Figure 18. Turn-on Rising Time vs. Temperature



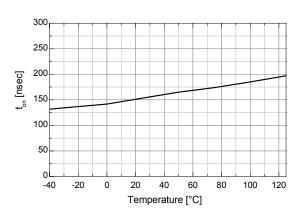
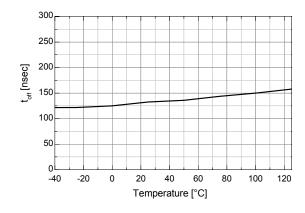


Figure 19. Turn-off Falling Time vs. Temperature

Figure 20. Turn-on Delay Time vs. Temperature



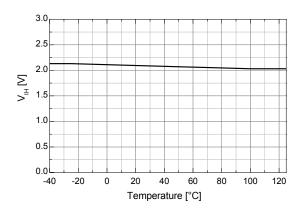
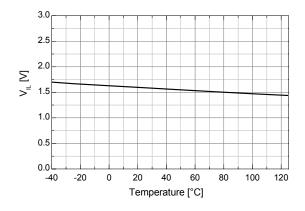


Figure 21. Turn-off Delay Time vs. Temperature

Figure 22. Logic Input High Voltage vs. Temperature



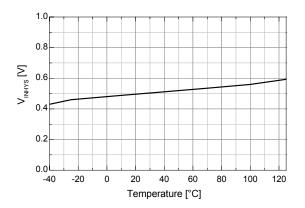
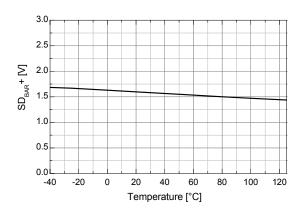


Figure 23. Logic Input Low Voltage vs. Temperature

Figure 24. Logic Input Hysteresis vs. Temperature



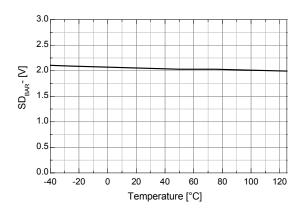
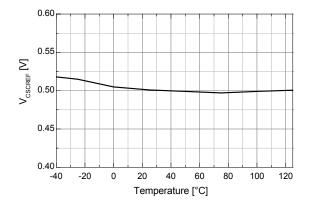


Figure 25. SD Positive Threshold vs. Temperature

Figure 26. SD Negative Threshold vs. Temperature



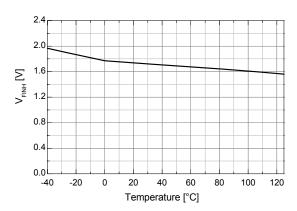
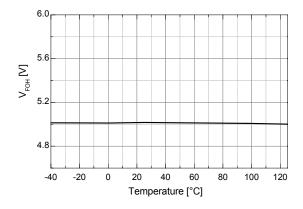


Figure 27. V<sub>CSCREF</sub> vs. Temperature

Figure 28. Fault Input High Voltage vs. Temperature



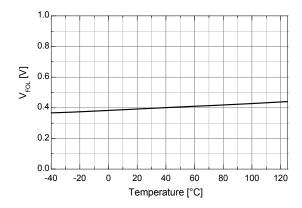
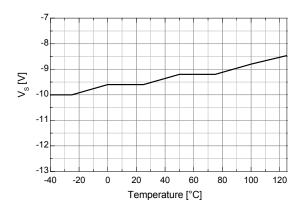


Figure 29. Fault Output High Voltage vs.
Temperature

Figure 30. Fault Output Low Voltage vs. Temperature



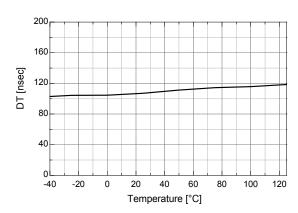


Figure 31. Allowable Negative V<sub>S</sub> Voltage for Signal Propagation to High Side vs. Temperature

Figure 32. Dead Time vs. Temperature

## **Switching Time Definitions**

The overall switching timing waveforms definition of FAN7384 as shown Figure 33.

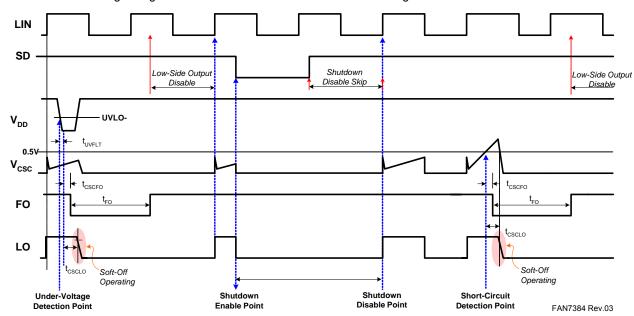


Figure 33. Switching Timing Waveforms Definition

### **Typical Application Information**

#### 1. Protection Function

#### 1.1 Under-Voltage Lockout (UVLO)

The high- and low-side drivers include under-voltage lockout (UVLO) protection circuitry that monitors the supply voltage ( $V_{DD}$ ) and bootstrap capacitor voltage ( $V_{BS}$ ) independently. It can be designed to prevent malfunction when  $V_{DD}$  and  $V_{BS}$  are lower than the specified threshold voltage. Moreover, the UVLO hysteresis prevents chattering during power supply transitions. If the supply voltage ( $V_{DD}$ ) maintains an under-voltage condition over under-voltage filtering times (typically 16 $\mu$ s), the fault and soft-off circuits are activated, as shown Figure 34.

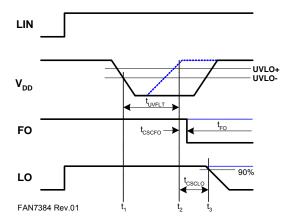


Figure 34. Waveforms for Under-Voltage Lockout

### 1.2 Shoot-Through Prevention Function

The FAN7384 has a shoot-through prevention circuitry that monitors the high- and low-side inputs. It can be designed to prevent outputs of high- and low-side turning on at same time, as shown Figure 35 and 36.

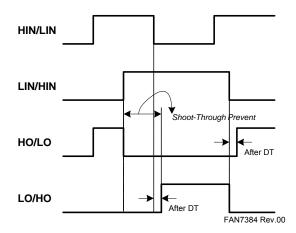


Figure 35. Waveforms for Shoot-Through Prevention

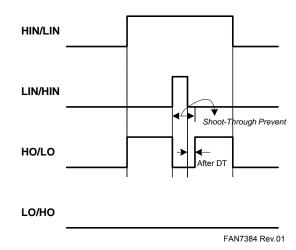


Figure 36. Waveforms for Shoot-Through Prevention

#### 1.3 Over-Current Protection Function

The FAN7384 has over-current detection circuitry that monitors the current-by-current sensing resistor connected from the low-side switch source ( $V_{\rm SL}$ ) to ground.

It is a built-in time-filler from the over-current event to prevent malfunction from a noise source, such as leading-edge pulse in inductive load application, as shown Figure 37.

The sensing current is calculated as follows:

$$I_{\rm CS} = \frac{V_{\rm CSCREF}}{R_{\rm CS}} [A] \tag{1}$$

where,

V<sub>CSCREF</sub>: Reference voltage of current sense comparator

R<sub>CS</sub>: Current sensing resistor

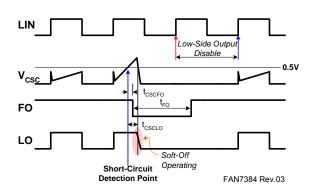


Figure 37. Waveforms for Short-Circuit Protection

### 2. Layout Considerations

For optimum performance, considerations must be taken during printed circuit board (PCB) layout.

### 2.1 Supply Capacitors

If the output stages are able to quickly turn on a switching device with a high value of current, the supply capacitors must be placed as close as possible to the device pins ( $V_{DD}$  and GND for the ground-tied supply,  $V_{B}$  and  $V_{S}$  for the floating supply) to minimize parasitic inductance and resistance.

### 2.2 Gate-Drive Loop

Current loops behave like antennae, able to receive and transmit noise. To reduce the noise coupling/emission and improve the power switch turn-on and off performance, gate-drive loops must be reduced as much as possible.

#### 2.3 Ground Plane

To minimize noise coupling, the ground plane should not be placed under or near the high-voltage floating side.

## **Package Dimensions**

### 14-SOP

Dimensions are in millimeters unless otherwise noted.

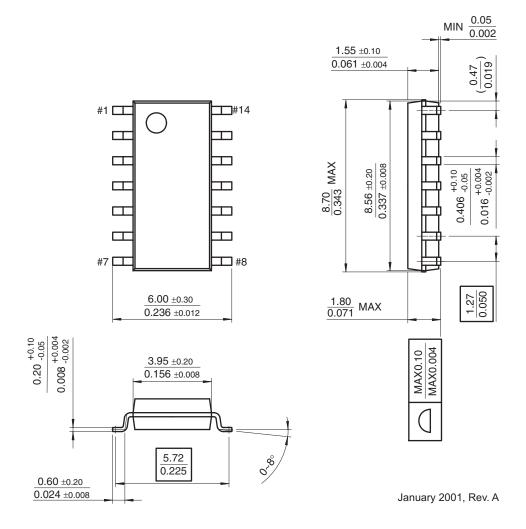


Figure 38. 14-Lead Small Outline Package (SOP)

#### **FAIRCHILD SEMICONDUCTOR TRADEMARKS**

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### PRODUCT STATUS DEFINITIONS

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